

## SI2325DS-T1-GE3-VB Datasheet

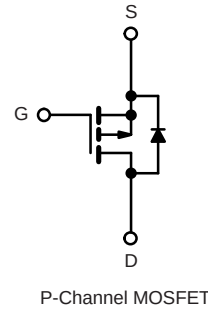
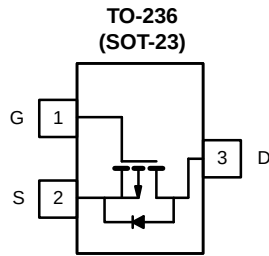
### P-Channel 60 V (D-S) MOSFET

#### PRODUCT SUMMARY

| $V_{DS}$ (V) | $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS(th)}$ (V) | $I_D$ (mA) |
|--------------|---------------------------|------------------|------------|
| - 60         | 3 at $V_{GS} = - 10$ V    | - 1 to - 3       | -500       |

#### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- High-Side Switching
- Low On-Resistance: 3  $\Omega$
- Low Threshold: - 2 V (typ.)
- Fast Switching Speed: 20 ns (typ.)
- Low Input Capacitance: 20 pF (typ.)
- Compliant to RoHS Directive 2002/95/EC


**RoHS**  
 COMPLIANT


#### ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted

| Parameter                                        | Symbol         | Limit                                        | Unit                 |
|--------------------------------------------------|----------------|----------------------------------------------|----------------------|
| Drain-Source Voltage                             | $V_{DS}$       | - 60                                         | V                    |
| Gate-Source Voltage                              | $V_{GS}$       | $\pm 20$                                     |                      |
| Continuous Drain Current <sup>a</sup>            | $I_D$          | $T_A = 25\text{ }^{\circ}\text{C}$<br>- 500  | mA                   |
|                                                  |                | $T_A = 100\text{ }^{\circ}\text{C}$<br>- 350 |                      |
| Pulsed Drain Current <sup>b</sup>                | $I_{DM}$       | -1500                                        |                      |
| Power Dissipation <sup>a</sup>                   | $P_D$          | $T_A = 25\text{ }^{\circ}\text{C}$<br>460    | mW                   |
|                                                  |                | $T_A = 100\text{ }^{\circ}\text{C}$<br>240   |                      |
| Maximum Junction-to-Ambient <sup>a</sup>         | $R_{thJA}$     | 350                                          | $^{\circ}\text{C/W}$ |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$ | - 55 to 150                                  | $^{\circ}\text{C}$   |

Notes:

a. Surface mounted on FR4 board.

b. Pulse width limited by maximum junction temperature.

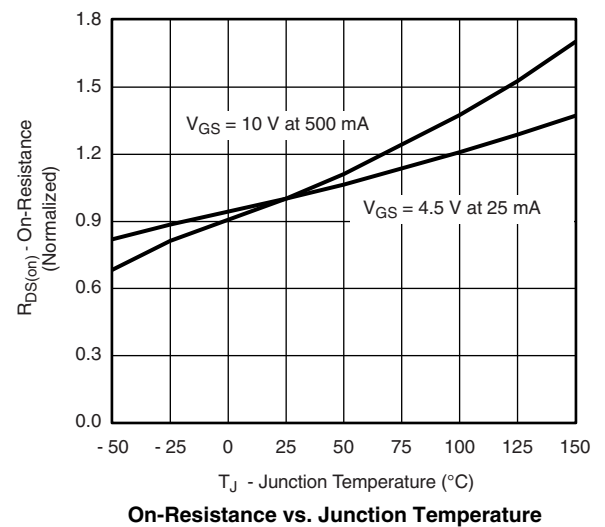
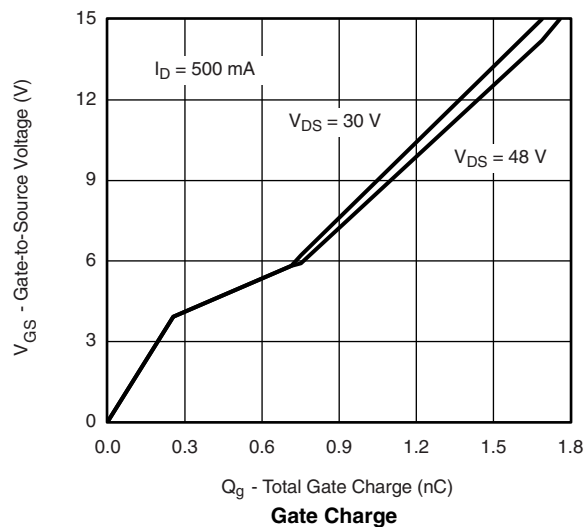
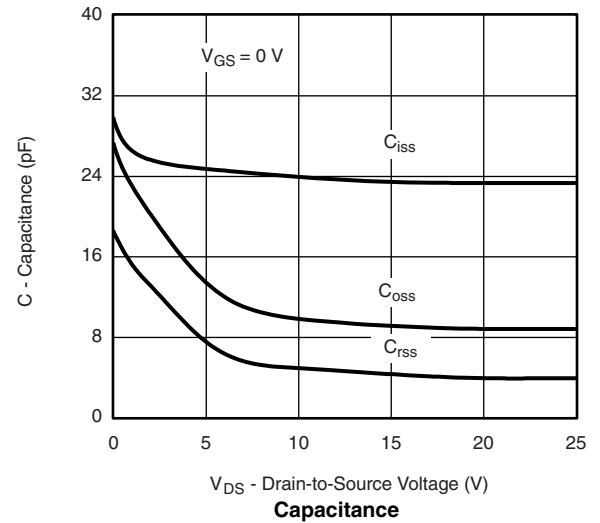
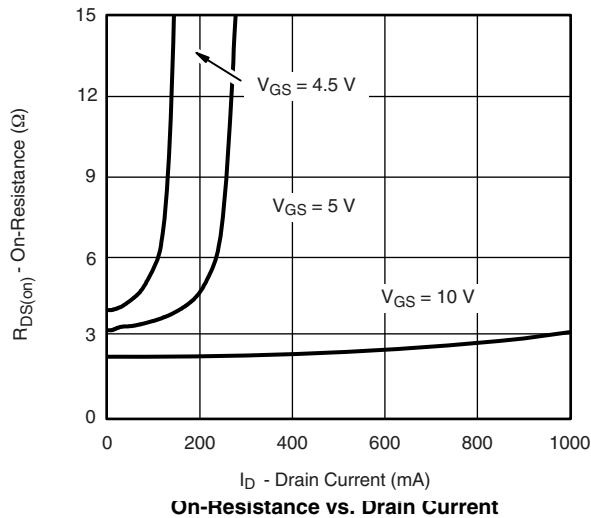
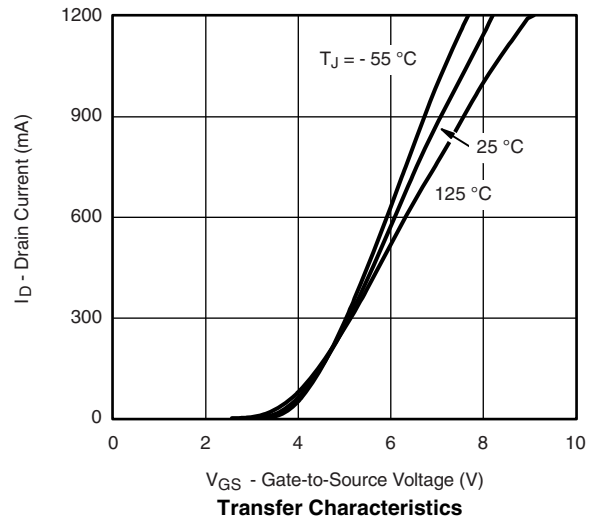
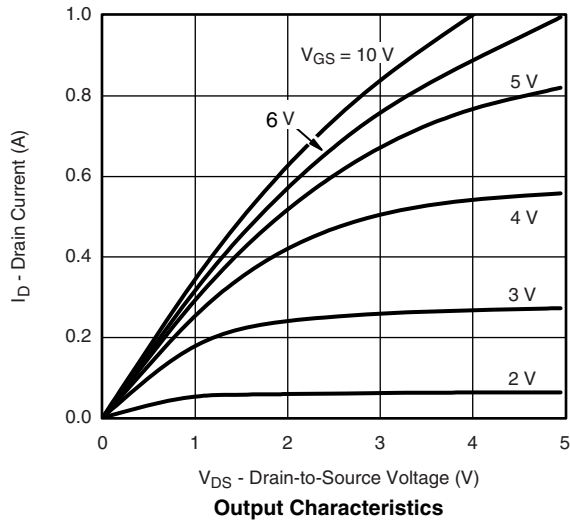
| SPECIFICATIONS T <sub>A</sub> = 25 °C, unless otherwise noted |                     |                                                                                                                                 |        |                   |       |      |
|---------------------------------------------------------------|---------------------|---------------------------------------------------------------------------------------------------------------------------------|--------|-------------------|-------|------|
| Parameter                                                     | Symbol              | Test Conditions                                                                                                                 | Limits |                   |       | Unit |
|                                                               |                     |                                                                                                                                 | Min.   | Typ. <sup>a</sup> | Max.  |      |
| Static                                                        |                     |                                                                                                                                 |        |                   |       |      |
| Drain-Source Breakdown Voltage                                | V <sub>DS</sub>     | V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 10 μA                                                                                 | - 60   |                   |       | V    |
| Gate-Threshold Voltage                                        | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA                                                                   | - 1    |                   | - 3   |      |
| Gate-Body Leakage                                             | I <sub>GSS</sub>    | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V                                                                                 |        |                   | ± 10  | μA   |
|                                                               |                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 10 V                                                                                 |        |                   | ± 200 | nA   |
|                                                               |                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 10 V, T <sub>J</sub> = 85 °C                                                         |        |                   | ± 500 |      |
|                                                               |                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 5 V                                                                                  |        |                   | ± 100 |      |
| Zero Gate Voltage Drain Current                               | I <sub>DSS</sub>    | V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V                                                                                 |        |                   | - 25  |      |
|                                                               |                     | V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C                                                         |        |                   | - 250 |      |
| On-State Drain Current <sup>a</sup>                           | I <sub>D(on)</sub>  | V <sub>GS</sub> = - 10 V, V <sub>DS</sub> = - 4.5 V                                                                             | - 50   |                   |       | mA   |
|                                                               |                     | V <sub>GS</sub> = - 10 V, V <sub>DS</sub> = - 10 V                                                                              | - 600  |                   |       |      |
| Drain-Source On-Resistance <sup>a</sup>                       | R <sub>DS(on)</sub> | V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 25 mA                                                                             |        | 4                 |       | Ω    |
|                                                               |                     | V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 100 mA                                                                             |        | 3                 |       |      |
|                                                               |                     | V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 100 mA, T <sub>J</sub> =125 °C                                                     |        | 9                 |       |      |
| Forward Transconductance <sup>a</sup>                         | g <sub>fs</sub>     | V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 100 mA                                                                             | 80     |                   |       | mS   |
| Diode Forward Voltage                                         | V <sub>SD</sub>     | I <sub>S</sub> = - 100 mA, V <sub>GS</sub> = 0 V                                                                                |        |                   | - 1.4 | V    |
| Dynamic                                                       |                     |                                                                                                                                 |        |                   |       |      |
| Total Gate Charge                                             | Q <sub>g</sub>      | V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = - 15 V<br>I <sub>D</sub> ≅ - 100 mA                                                 |        | 2.0               |       | nC   |
| Gate-Source Charge                                            | Q <sub>gs</sub>     |                                                                                                                                 |        | 1.2               |       |      |
| Gate-Drain Charge                                             | Q <sub>gd</sub>     |                                                                                                                                 |        | 0.8               |       |      |
| Input Capacitance                                             | C <sub>iss</sub>    | V <sub>DS</sub> = - 25 V, V <sub>GS</sub> = 0 V<br>f = 1 MHz                                                                    |        | 23                |       | pF   |
| Output Capacitance                                            | C <sub>oss</sub>    |                                                                                                                                 |        | 10                |       |      |
| Reverse Transfer Capacitance                                  | C <sub>rss</sub>    |                                                                                                                                 |        | 5                 |       |      |
| Switching <sup>b</sup>                                        |                     |                                                                                                                                 |        |                   |       |      |
| Turn-On Time                                                  | t <sub>d(on)</sub>  | V <sub>DD</sub> = - 25 V, R <sub>L</sub> = 150 Ω<br>I <sub>D</sub> ≅ - 200 mA, V <sub>GEN</sub> = - 10 V, R <sub>g</sub> = 10 Ω |        | 20                |       | ns   |
| Turn-Off Time                                                 | t <sub>d(off)</sub> |                                                                                                                                 |        | 35                |       |      |

Notes:

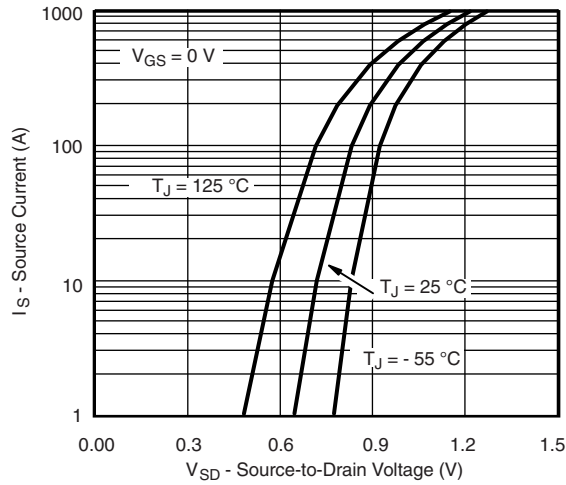
a. Pulse test:  $PW \leq 300\text{ }\mu\text{s}$  duty cycle  $\leq 2\%$ .

b. Switching time is essentially independent of operating temperature.

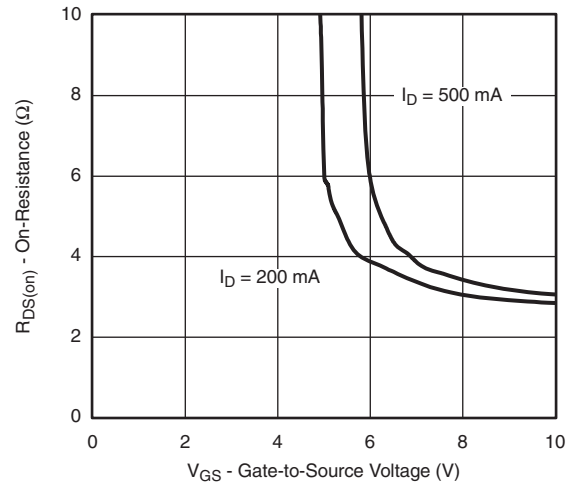
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


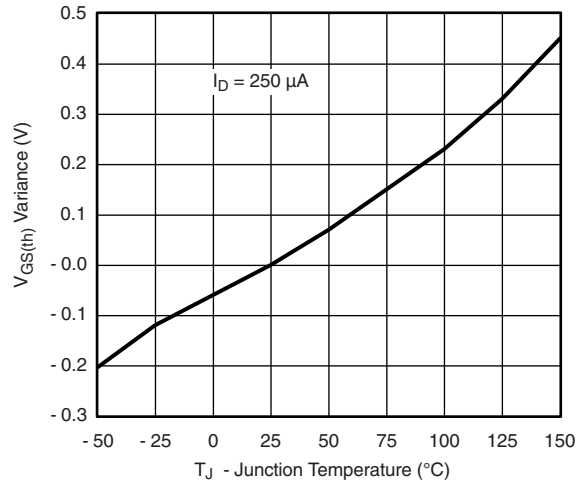
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



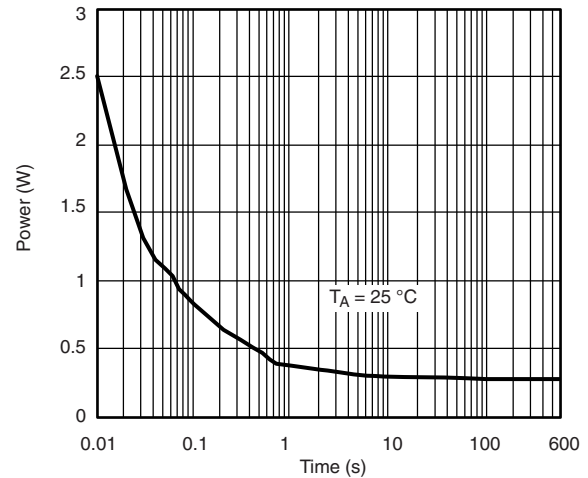
Source-Drain Diode Forward Voltage



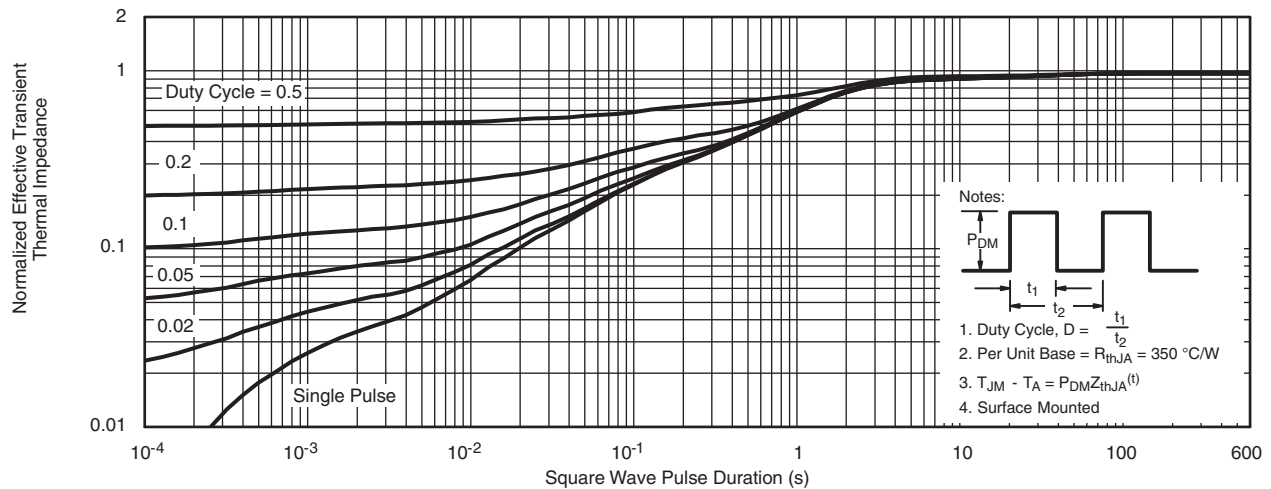
On-Resistance vs. Gate-Source Voltage



Threshold Voltage Variance Over Temperature

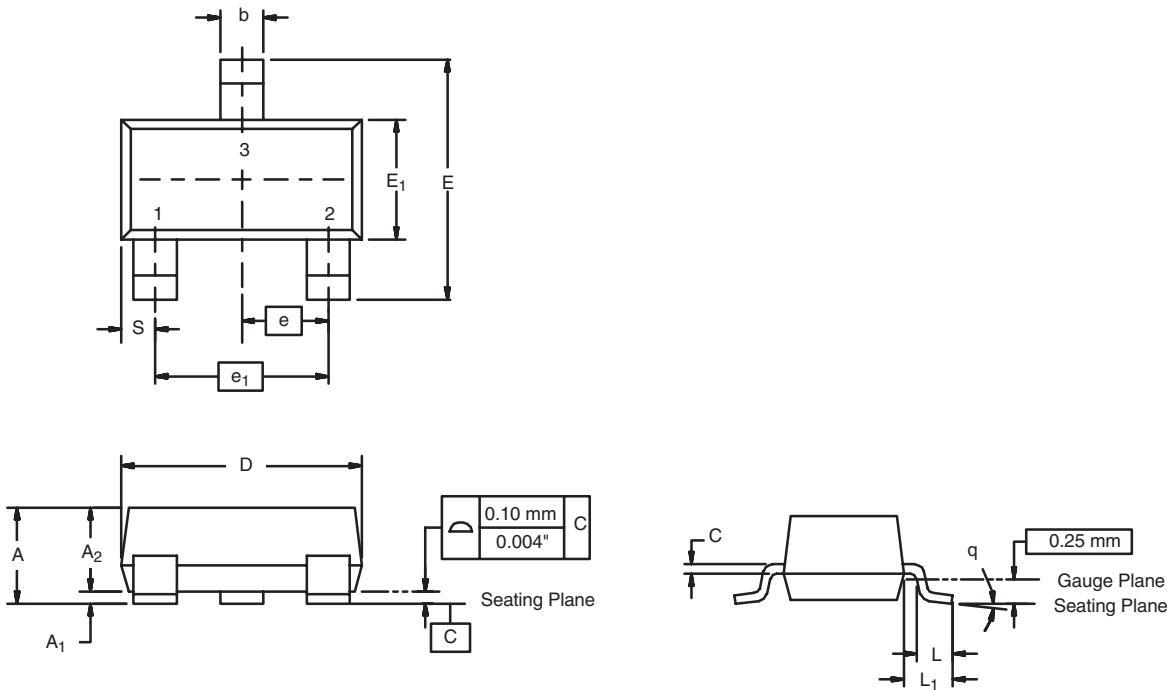


Single Pulse Power, Junction-to-Ambient



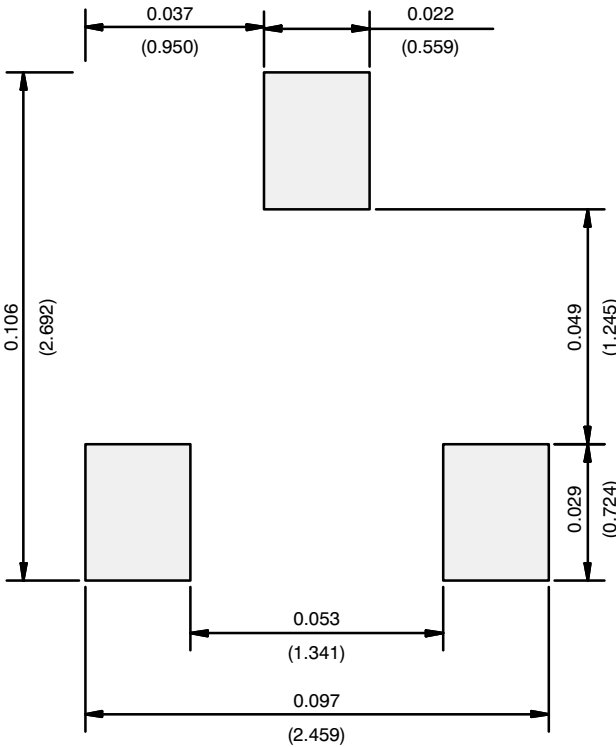
Normalized Thermal Transient Impedance, Junction-to-Ambient

**SOT-23 (TO-236): 3-LEAD**



| Dim                                         | MILLIMETERS |      | INCHES     |       |
|---------------------------------------------|-------------|------|------------|-------|
|                                             | Min         | Max  | Min        | Max   |
| A                                           | 0.89        | 1.12 | 0.035      | 0.044 |
| A <sub>1</sub>                              | 0.01        | 0.10 | 0.0004     | 0.004 |
| A <sub>2</sub>                              | 0.88        | 1.02 | 0.0346     | 0.040 |
| b                                           | 0.35        | 0.50 | 0.014      | 0.020 |
| c                                           | 0.085       | 0.18 | 0.003      | 0.007 |
| D                                           | 2.80        | 3.04 | 0.110      | 0.120 |
| E                                           | 2.10        | 2.64 | 0.083      | 0.104 |
| E <sub>1</sub>                              | 1.20        | 1.40 | 0.047      | 0.055 |
| e                                           | 0.95 BSC    |      | 0.0374 Ref |       |
| e <sub>1</sub>                              | 1.90 BSC    |      | 0.0748 Ref |       |
| L                                           | 0.40        | 0.60 | 0.016      | 0.024 |
| L <sub>1</sub>                              | 0.64 Ref    |      | 0.025 Ref  |       |
| S                                           | 0.50 Ref    |      | 0.020 Ref  |       |
| q                                           | 3°          | 8°   | 3°         | 8°    |
| ECN: S-03946-Rev. K, 09-Jul-01<br>DWG: 5479 |             |      |            |       |

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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